Implicit time integration methods and inexact Newton methods: application to chemical vapor deposition

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Vuik, Van Veldhuizen and Kleijn Implicit time integration methods and inexact Newton method



Outline







Chemical Vapor Deposition Transport Model

Chemical Vapor Deposition

- Synthesizes thin solid film from gaseous phase by chemical reaction on solid material
- Reactions driven by thermal energy



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Conclusions

Chemical Vapor Deposition

Chemical Vapor Deposition

Applications



- Semiconductors
- Solar cells
- Optical, mechanical and decorative coatings

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Chemical Vapor Deposition Transport Model

Transport Model for CVD

Mathematical Model

- Continuity equation
- Navier-Stokes equations
- Energy equation in terms of temperature
- Species equation
- Ideal gas law

Species Equation

• Advection Diffusion Reaction Equation

$$\frac{\partial(\rho\omega)}{\partial t} = \nabla \cdot (\rho v\omega) + \nabla \cdot (\mathbb{D}\nabla\omega) + m \sum_{k=1}^{\text{\#reactions}} \nu_k R_k^G$$

Implicit time integration methods and inexact Newton method



Conclusions

Chemical Vapor Deposition Transport Model

Transport Model for CVD

Reaction Rate

Net molar reaction rate

$$R_{k}^{G} = k_{k,fw} \sum_{i=1}^{S} \|\nu_{i,s}\| c_{i} - k_{k,bw} \sum_{i=1}^{S} \|-\nu_{i,s}\| c_{i}$$

• Modified Law of Arrhenius $k_{k,fw} = A_k \cdot T^{\beta_k} e^{-\frac{E_k}{RT}}$ • max $(k_{k,fw})/\min(k_{k,bw}) = 10^{28}$

Properties Mathematical Model of CVD

- Consists of (#species -1 + 3 + d) coupled PDEs
- Stiff nonlinear system of species equations



Properties Positivity Nonlinear Solvers Linear Solvers

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Numerical Methods

Properties

- Stiff Problem → Stable Time Integration
- Positivity (= preservation of non-negativity): Negative Species can cause blow up of the solution
- Efficiency / Robustness
- Method of Lines approach

Properties Positivity Nonlinear Solvers Linear Solvers



Positivity

Mass fractions

A natural property for mass fractions is their non-negativity

Positivity of mass fractions should hold for ...

- Model equations
- Spatial discretization: Hybrid scheme Introduces locally first order upwinding
- Time integration
- Iterative solvers: (Non)linear solver

Properties Positivity Nonlinear Solvers Linear Solvers



Positivity for ODE systems

Euler Backward

•
$$W_{n+1} - W_n = \tau F(t_{n+1}, W_{n+1})$$

Unconditionally stable (A-stable/ stiffly stable)

Theorem (Hundsdorfer, 1996)

Euler Backward is positive for any step size τ

Theorem (Bolley and Crouzeix, 1970)

Any unconditionally positive time integration is at most first order accurate

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Nonlinear Solvers

Inexact Newton to solve F(x) = 0

Let x_0 be given. **FOR** k = 1, 2, ... until 'convergence' Find some $\eta_k \in [0, 1)$ and s_k that satisfy

$$\|\boldsymbol{F}(\boldsymbol{x}_k) + \boldsymbol{F}'(\boldsymbol{x}_k)\boldsymbol{s}_k\| \leq \eta_k \|\boldsymbol{F}(\boldsymbol{x}_k)\|.$$

Set $x_{k+1} = x_k + s_k$. ENDFOR

Properties Positivity Nonlinear Solvers Linear Solvers

Nonlinear Solvers

Inexact Newton Condition

$$\|F(\mathbf{x}_k) + F'(\mathbf{x}_k)\mathbf{s}_k\| \leq \eta_k \|F(\mathbf{x}_k)\|$$

Choices for Forcing Term

•
$$\eta_k = \frac{\left| \|F(x_k)\| - \|F(x_{k-1}) - F'(x_{k-1})s_{k-1}\| \right|}{\|F(x_{k-1})\|}$$

• $\eta_k = \gamma \frac{\|F(x_k)\|^2}{\|F(x_{k-1})\|^2}$

Properties Positivity Nonlinear Solvers Linear Solvers



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Properties Positivity Nonlinear Solvers Linear Solvers

Lexicographic ordering (left) and Alternate blocking per grid point(right)



Properties Positivity Nonlinear Solvers Linear Solvers

Iterative Linear Solver

- Right preconditioned BiCGStab
- $\bullet\,$ 'Heavy' chemistry terms \rightarrow diagonal blocks

Incomplete Factorization: ILU(0)

	lexico	alternate blocking		
Number of	graphic	per gridpoint		
F	220	197		
Newton iters	124	111		
Linesearch	12	7		
Rej. time steps	0	0		
Acc. time steps	36	36		
CPU Time	400	300		
linear iters	444	346		

Properties Positivity Nonlinear Solvers Linear Solvers

Preconditioners: Lumping

Important: Lumping per species



Properties Positivity Nonlinear Solvers Linear Solvers

Preconditioners: Block Diagonal



- 'natural' blocking over species
- series of uncoupled systems → LU factorization per subsystem

Properties Positivity Nonlinear Solvers Linear Solvers

Preconditioners: Block D-ILU

- Block version of the matrix derived from central differences on a Cartesian product grid
- To compute: inverse of a diagonal block \rightarrow solve linear system directly
- Storage: factorization of diagonal blocks



Kleijn's Benchmark Problem

Computational Domain



- Axisymmetric
- 0.1 mole% SiH₄ at the inflow
- Rest is carrier gas helium He
- Susceptor does not rotate

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Kleijn's Benchmark Problem



- grid sizes: 35 × 32 up to 70 × 82 grid points
- Temperature: Inflow 300 K Susceptor 1000 K
- Uniform velocity at inflow



Kleijn's Benchmark Problem

Chemistry Model: 16 species, 26 reactions [1]

- Above heated wafer SiH₄ decomposes into SiH₂ and H₂
- Chain of 25 homogeneous gas phase reactions
- Including the carrier gas the gas mixture contains 17 species, of which 14 contain silicon atoms
- Irreversible surface reactions at the susceptor leads to deposition of solid silicon

[1] M.E. Coltrin, R.J. Kee and G.H. Evans, A Mathematical Model of the Fluid Mechanics and Gas-Phase Chemistry

in a Rotating Chemical Vapor Deposition Reactor, J. Electrochem. Soc., 136, (1989)

Numerical Results

ntegration	statistics:	35×32	arid
			<u> </u>

	ILU(0) Lumped		block	block	block direct	
		Jac	DILU	diag	solver	
F	197	310	210	3181	190	
Newton	111	185	112	1239	94	
linesearch	7	20	13	0	11	
Rej. time step	0	3	0	459	1	
Acc. time step	36	41	36	774	38	
lin iters	346	3693	676	3315		
CPU	300	590	380	3250	6500	



Numerical Results

Integration statistics: 70×82 grid

	ILU(0)	Lumped	block	block
		Jac	DILU	diag
F	869	nf	613	nf
Newton	476	nf	327	nf
linesearch	127	nf	106	nf
Rej. time step	15	nf	0	nf
Acc. time step	62	nf	37	nf
lin iters	8503	nf	2036	nf
CPU	7400	nf	5300	nf

Direct solver is not feasable.





Kleijn's Benchmark Problem

Validation: Species mass fraction along the symmetry axis



- solid: Kleijn's solutions
- circles: our solutions



Kleijn's Benchmark Problem

Validation: Radial profiles of total steady state deposition rate



- wafer temperature from 900 K up to 1100 K
- solid: Kleijn's solutions
- circles: our solutions



Kleijn's Benchmark Problem





Kleijn's Benchmark Problem

Transient behavior of deposition rates





Conclusions and Future Research

Conclusions

- Euler Backward is unconditionally positive, but Inexact Newton does not preserve this property
- Alternate blocking per grid point is more effective
- Easy preconditioners are effective for 2D problem
- Chemistry source terms should be in the preconditioner



Conclusions and Future Research

Future Research

- 3D transient simulations
- How to preserve positivity when iterative linear solvers are used ?
- More realistic chemistry/surface chemistry models
- Steady state solver



References and Contact Information

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References and Contact Information

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